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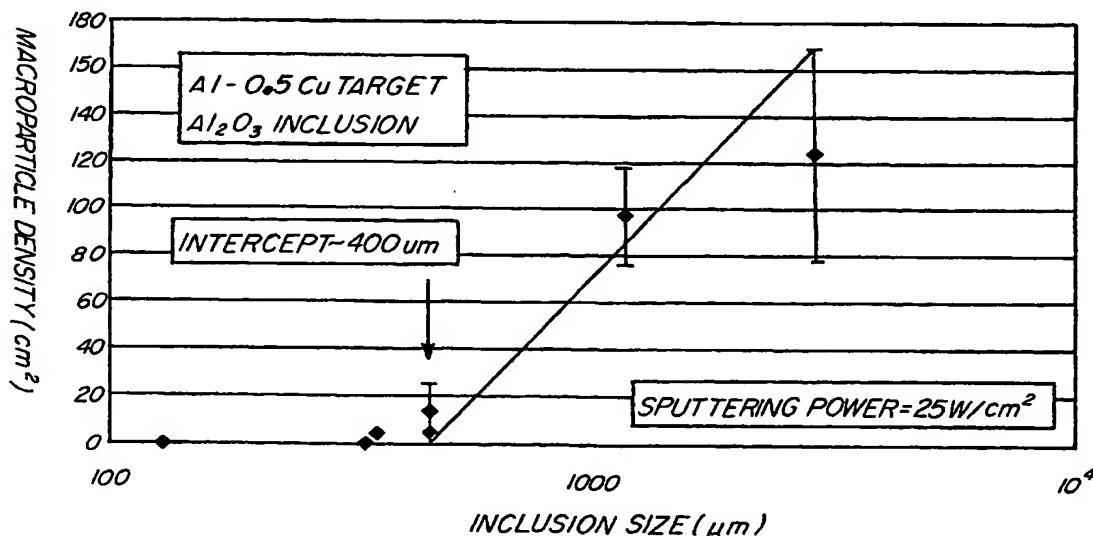
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(54) Title: SPUTTER TARGETS AND METHODS OF MANUFACTURING SAME TO REDUCE PARTICULATE EMISSION
DURING SPUTTERING

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(57) Abstract: Methods for reducing inclusion content of sputter targets and targets so produced are disclosed. Inclusions (93) may be reduced by adding a small amount of Si to the molten A1 or molten A1 alloy followed by filtering of the molten metals through a filter medium (175). Targets having substantially no inclusions (93) therein of greater than about 400μm are especially useful in the sputtering of large flat panel displays and result, upon sputtering, in a reduction in the amount of macroparticles sputtered onto the substrate.